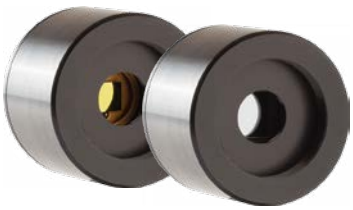
PRESENTATION

OVERVIEW OF THE DIFFERENT MODELS

Our photo detectors are offered for both power or energy measurements. Measure as low as a few femtojoules in energy or a few picowatts in power.

FOR POWER MEASUREMENTS

The section below lists all the photo detectors used for power measurements. The corresponding comparison table and power range chart are given at the next page.



PH-B

- 5 and 10 mm Ø Apertures
- UV-Silicon and Germanium Sensors
- Very Low Powers, down to the pW level

NOISE DOWN TO THE pW LEVEL

See page **110**

Available with integra

PH

- High Power Photo Detectors for measurements up to 750 mW
- Available from UV to IR
- Silicon, UV-Silicon and Germanium Sensors
- OD1/OD2 Attenuators Available

HIGH POWER Si OR Ge SENSORS

See page **112**

PRONTO-Si

- Compact Low Power Probe up to 300 mW
- 10 x 10 mm Aperture
- Continuous Measurements
- Integrated OD1 Slide-in Attenuator

POCKET-SIZED
COLOR TOUCH SCREEN DISPLAY
SCREEN AND SENSOR ARE PROTECTED WHEN YOU FLIP IT CLOSE
USE IT IN VERY TIGHT SPACES (ONLY 6 mm AT THE SENSOR)

See page **116**

FOR ENERGY MEASUREMENTS

The section below lists all the photo detectors used for energy measurements. The corresponding comparison table and energy range chart are given at the next page.

Available with integra

PE-B

- 3, 5 and 10 mm Ø Apertures
- Germanium and InGaAs Sensors
- Lowest Noise Level of ALL Energy Detectors (8 fJ with PE3B-Si)

8 fJ NOISE LEVEL

See page **114**

COMPARISON TABLE

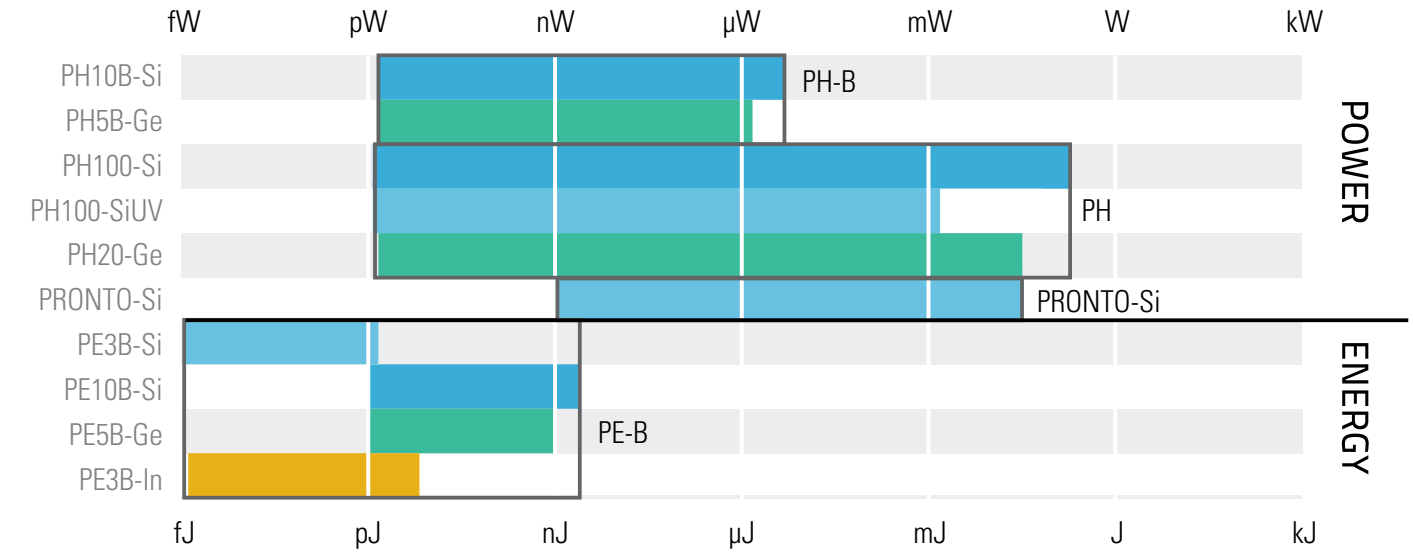
FOR POWER MEASUREMENTS

MODEL	PMAX	NOISE LEVEL	λMIN	λMAX	SENSOR TYPE	APERTURE	SEE PAGE
PH5B-Ge	40 µW	40 pW	800 nm	1.65 µm	Germanium	5 mm Ø	110
PH10B-Si	200 µW	50 pW	210 nm	1.08 µm	UV-Silicon	10 mm Ø	110
PH100-SiUV	4 mW	10 pW	210 nm	1.08 µm	UV-Silicon	10 mm Ø	112
PH100-SiUV-OD.3	11 mW	30 pW	210 nm	1.08 µm	UV-Silicon	10 mm Ø	112
PH100-SiUV-OD1	38 mW	100 pW	400 nm	1.08 µm	UV-Silicon	10 mm Ø	112
PH20-Ge	30 mW	60 pW	800 nm	1.65 µm	Germanium	5 mm Ø	112
PH100-Si-HA	36 mW	10 pW	350 nm	1.08 µm	Silicon	10 mm Ø	112
PH100-Si-HA-OD1	300 mW	100 pW	420 nm	1.08 µm	Silicon	10 mm Ø	112
PH20-Ge-OD1	300 mW	600 pW	900 nm	1.65 µm	Germanium	5 mm Ø	112
PRONTO-Si	300 mW	10 pW	320 nm	1.1 µm	Silicon	10 X 10 mm	116
PH20-Ge-OD2	500 mW	6 nW	950 nm	1.65 µm	Germanium	5 mm Ø	105
PH100-Si-HA-OD2	750 mW	1 nW	630 nm	1.1 µm	Silicon	10 mm Ø	112

FOR ENERGY MEASUREMENTS

MODEL	EMAX	NOISE LEVEL	λMIN	λMAX	SENSOR TYPE	APERTURE	SEE PAGE
PE3B-Si	30 pJ	8 fJ	210 nm	1.08 µm	UV-Silicon	3 mm Ø	114
PE3B-In	300 pJ	30 fJ	900 nm	1.7 µm	InGaAs	3 mm Ø	114
PE5B-Ge	3 nJ	1 pJ	800 nm	1.65 µm	Germanium	5 mm Ø	114
PE10B-Si	150 nJ	1.5 pJ	210 nm	1.08 µm	UV-Silicon	10 mm Ø	114

Available with INTEGRA all-in-one detector + meter



Silicon/UV-Silicon Sensors
190 - 1100 nm

Germanium Sensor
800 - 1650 nm

InGaAs Sensor
900 - 1700 nm

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